Citations for Target : **Si3N4**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1973	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. **'Ranges and Distributions of Ions Implanted into Dielectrics'** ***B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 225-41 (1973)*** Comment : *R.dR. (140-300 keV) Zn, Ga, As, Se, Cd, Te, Zn -> Si, Si3N4, Al2O3*	**1973-Chu 2** 0539
1973	Combasson, J. L. Bernard, J. Guernet, G. **'Physical Profile Measurements in Insulating Layers using the Ion Analyzer'** ***B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 285-94 (1973)*** Comment : *R,dR. 60, 100 keV B -> SiO2; 20, 40 keV B -> Si3N4; 60 keV B -> Si (Amorphous)*	**1973-Comb** 0537
1975	Ziegler, J. F. Chu, W. K. Feng, J. S. **'Empirical Corrections to the Energy Loss of 4He Ions in Oxides'** ***Appl. Phys. Letters, 27, 387-90 (1975)*** Comment : *S. 2 MeV He -> Fe2O3, Fe3O4, MgO, Al2O3, SiO2, Si3N4 All Rel. To Metal*	**1975-Zieg** 0880
1976	Ziegler, J. F. Chu, W. K. Feng, J. S. **'Evidence of Solid State Effects in the Energy Loss of 4He Ions in Matter'** ***Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 15-27 (1976)*** Comment : *S. 2 MeV He -> Fe2O3, Fe3O4, MgO, Al2O3, SiO2, Si3N4*	**1976-Zieg2** 0851
1979	Doyle, B. L. Peercy, P. S. **'Technique for Profiling 1H with 2.5 MeV van de Graaff Accelerators.'** ***Appl. Phys. Letters, 34, 811-813 (1979)*** Comment : *R. 1-3 MeV H -> Si3N4, Si*	**1979-Doyl** 1135
1979	Muller, G. Trapp, M. Schimko, R. Richter, C. E. **'Measurement of Range Distributions of Zinc and Nitrogen Ions in Multiple-Layer Substrates with Secondary Ion Microprobe'** ***Phys. Stat. Sol. A, 51, 87-92 (1979)*** Comment : *R, dR. 50-300 keV N, Zn ->SiO2-GaAs(1-X)P(X), SiO2-Si3N4*	**1979-Mull** 1237